

1N5807/US, 1N5809/US, 1N5811/US

ULTRAFAST RECOVERY RECTIFIERS

TECHNICAL DATA DATA SHEET 127, REV. H.6

AVAILABLE AS 1N, JAN, JANTX, JANTXV JANS JAN EQUIVALENT\* SJ\*, SX\*, SV\*, SS\*

# **Ultrafast Recovery Rectifiers**

Qualified per MIL-PRF-19500/477

### **DESCRIPTION:**

This voidless hermetically sealed ultrafast recovery rectifier diode series is military qualified per Mil-PRF-19500/477 and is targeted for commerical and military aircraft, military vehicles, shipboard markets, space and all other high reliability applications.

### **FEATURES / BENEFITS:**

- ✓ Hermetic, non-cavity glass package
- ✓ Category I Metallurgically bonded
- ✓ All devices are 100% hot solder dipped
- ✓ JAN/ JANTX/JANTXV available per MIL-PRF-19500/477

### **MAXIMUM RATINGS**

- ✓ Operating and Storage Temperature: -65°C to +175°C
- ✓ Thermal Resistance: 22 °C (junction to lead)
- ✓ Thermal Resistance: 6.5 °C (junction to endcap)
- ✓ Forward surge current:125A @ 8.3 ms half-sine

### **ELECTRICAL CHARACTERISTICS**

TYPE NUMBER	WORKING PEAK REVERSE VOLTAGE	AVG RECTIFIED CURRENT <sup>1</sup>	MAXIMUM REVERSE CURRENT @ PIV		MAX. PEAK FORWARD VOLTAGE (PULSED)	MAXIMUM SURGE CURRENT <sup>2</sup> I <sub>FSM</sub>	MAXIMUM REVERSE RECOVERY TIME <sup>3</sup>
		Amps	μAn	nps	V <sub>F</sub> @ 4A		Trr
	Volts	55°C	25°C	125°C	V	Amps	nsec
1N5807/US 1N5809/US 1N5811/US	50 100 150	6.0	5	525	.875	125	30

Note 1:  $T_{EC} = T_L$  at L=0 or  $T_{end tab}$  f or US suffix devices. Derate at 60mA/°C for  $T_L$  above 75°C. Note 2:  $I_0 = 3A$ , 8.3ms surge Note 3:  $I_F=1A$ ,  $I_{RM}=1A$ ,  $I_{R(REC)}=.10A$ 

\*Sensitron **space equivalent diodes** are manufactured and screened to MIL-PRF-19500 flow and guidelines starting from wafer fabrication through assembly and testing using our internal specification.

## <u>SENSITRON</u> SEMICONDUCTOR

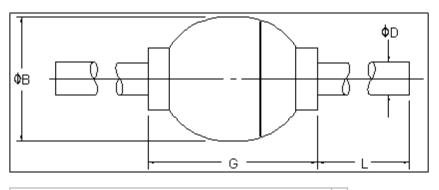
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### PACKAGE DIMENSIONS (inches/mm)

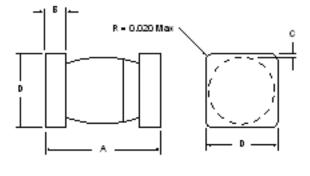
AXIAL



PACKAGE   DIMENSIONS - INCHES ( MILLIMETERS)					
STYLE	φB	φD	G	L	
304	.115/.142 2.92/3.61	.036/.042 .94/1.07	.130/.300 3.30/7.62	.90/1.30 22.9/33.0	

MELF (Add "US" to Part Number)

MELF PACKAGE OUTLINES





Note: Cathode side of device is indicated by a dark band marked on body.

PACKAGE STYLE	E DIMENSIONS - INCHES / MILLIMETERS				
	A	B	C	D	
MELF-8	.200/.225 5.0/5.8	0.019/.028 .48/.72	.003 Min .076 Min	.1377.148 3.4/3.8	

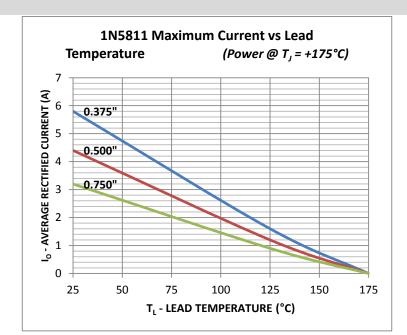
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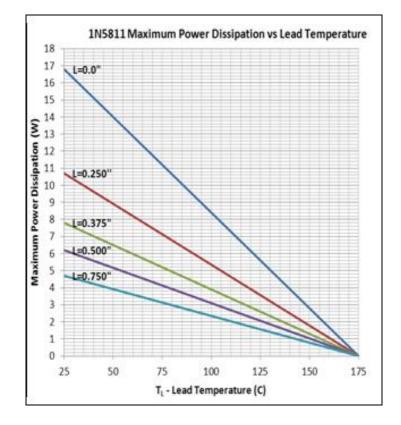
## SENSITRON SEMICONDUCTOR

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#### **GRAPHS**:





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#### PART ORDERING INFORMATION

The following part numbers can be purchased in either axial or surface mount devices and screened and tested to the military screening flow. The parts are marked in accordance with the testing performed, example:

		*Available with silver leads (SS5811-AG)
Sensitron Screening Level	*Part Number Leaded Package (example for 1N5811)	*Part Number Surface Mount Package (example for 1N5811US)
1N	1N5811	1N5811US
JAN	JAN1N5811	JAN1N5811US
JANTX	JANTX1N5811	JANTX1N5811US,
JANTXV	JANTXV1N5811	JANTXV1N5811US
SJ	SJ5811	SJ5811US
SX	SX5811	SX5811US
SV	SV5811	SV5811US
JANS	JANS1N5811	JANS1N5811US
SS	SS5811	SS5811US

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